

Listing of Claims:

1. (previously presented) A method of forming storage nodes in a dynamic random access memory (DRAM) on a semiconductor wafer, the semiconductor wafer comprising a substrate, a thin film layer positioned on
5 the substrate, and a photoresist layer positioned on the thin film layer, the method comprising:

performing a first exposure process to form first exposure regions that are lines parallel with each other and separated by unexposed parallel lines on the photoresist layer;

10 performing a second exposure process to form second exposure regions on the photoresist layer that cut the unexposed parallel lines, and the second exposure regions do not overlap the first exposure regions;

performing a development process on the first exposure regions and the second exposure regions of the photoresist layer;

15 removing the first exposure regions and the second exposure regions of the photoresist layer to form an array photoresist layer on the thin film layer; and

using the array photoresist layer as a mask to perform an etching process to remove portions of the thin film layer not covered by the array
20 photoresist layer so as to form an array thin film layer, the array thin film layer being used as the storage nodes in the DRAM.

2. (Original) The method of claim 1 wherein the method is used to prevent rounding corner effects, end-of-line shortening, or other optical proximity
25 effects to patterns of the photoresist layer.

3-6. (cancelled)